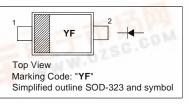
SILICON SCHOTTKY BARRIER DIODE

Features

- Low forward voltage drop and suitable for high effifiency rectifying
- Ultra small resin package is suitable for high density surface mounting and high speed assembly

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	30	V
Mean Rectifying Current	Io	100	mA
Non-Repetitive Peak Forward Surge Current (8.3 ms Single Half Sine Wave)	I _{FSM}	E MMM.	А
Junction Temperature	T _j	125	°C
Storage Temperature Range	T _{stg}	- 55 to + 125	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I _F = 100 mA	V _F	0.44	V
Reverse Current at V _R = 30 V	I _R	50	μA











Fig.1 Forward current Vs. Forward voltage

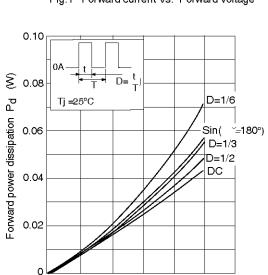


Fig.3 Forward power dissipation Vs. Forward current

Forward current IF (A)

0.06 0.08 0.10

0.12

0

0.02

0.04

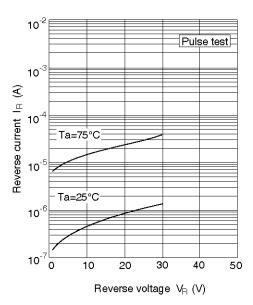


Fig.2 Reverse current Vs. Reverse voltage

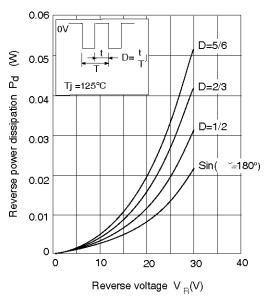


Fig.4 Reverse power dissipation Vs. Reverse voltage

SEMTECH ELECTRONICS LTD.











PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323

